Hisashi Murakami

List of Publications by Citations

134	3,472	24	56
papers	citations	h-index	g-index
143	4,080	1.8	5.34
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
134	Recent progress in Ga2O3power devices. *Semiconductor Science and Technology*, **2016**, 31, 034001	1.8	577
133	1-kV vertical Ga2O3 field-plated Schottky barrier diodes. *Applied Physics Letters*, **2017**, 110, 103506	3.4	322
132	Homoepitaxial growth of □Ga2O3layers by halide vapor phase epitaxy. *Applied Physics Express*, **2015**, 8, 015503	2.4	220
131	Temperature-dependent capacitance□oltage and current□oltage characteristics of Pt/Ga2O3 (001) Schottky barrier diodes fabricated on n□Ga2O3 drift layers grown by halide vapor phase epitaxy. *Applied Physics Letters*, **2016**, 108, 133503	3.4	210
130	State-of-the-art technologies of gallium oxide power devices. *Journal Physics D: Applied Physics*, **2017**, 50, 333002	3	153
129	Current status of Ga2O3power devices. *Japanese Journal of Applied Physics*, **2016**, 55, 1202A1	1.4	132
128	Anisotropy, phonon modes, and free charge carrier parameters in monoclinic □gallium oxide single crystals. *Physical Review B*, **2016**, 93,	3.3	107
127	Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport. *Applied Physics Express*, **2012** , 5, 055504	2.4	100
126	Current Aperture Vertical $beta$ -Ga2O3 MOSFETs Fabricated by N- and Si-Ion Implantation Doping. *IEEE Electron Device Letters*, **2019**, 40, 431-434	4.4	96
125	Acceptor doping of □Ga2O3 by Mg and N ion implantations. *Applied Physics Letters*, **2018**, 113, 102103	3.4	93
124	Halide vapor phase epitaxy of Si doped □Ga2O3 and its electrical properties. *Thin Solid Films*, **2018**, 666, 182-184	2.2	82
123	Thermodynamic study of □Ga2O3 growth by halide vapor phase epitaxy. *Journal of Crystal Growth*, **2014**, 405, 19-22	1.6	77
122	. *IEEE Electron Device Letters*, **2019**, 40, 1487-1490	4.4	71
121	Hydride vapor phase epitaxy of AlN: thermodynamic analysis of aluminum source and its application to growth. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2498-2501		63
120	Al- and N-polar AlN layers grown on c-plane sapphire substrates by modified flow-modulation MOCVD. *Journal of Crystal Growth*, **2007**, 305, 360-365	1.6	58
119	Polarity dependence of AlN {0001} decomposition in flowing H2. *Journal of Crystal Growth*, **2007**, 305, 366-371	1.6	55
118	All-ion-implanted planar-gate current aperture vertical Ga2O3 MOSFETs with Mg-doped blocking layer. *Applied Physics Express*, **2018**, 11, 064102	2.4	50

117	Electronic properties of the residual donor in unintentionally doped Ga2O3. *Journal of Applied Physics*, **2016**, 120, 235703	2.5	44
116	Investigation of void formation beneath thin AlN layers by decomposition of sapphire substrates for self-separation of thick AlN layers grown by HVPE. *Journal of Crystal Growth*, **2010**, 312, 2530-2536	1.6	39
115	. *IEEE Electron Device Letters*, **2020**, 41, 296-299	4.4	38
114	Structural and Optical Properties of Carbon-Doped AlN Substrates Grown by Hydride Vapor Phase Epitaxy Using AlN Substrates Prepared by Physical Vapor Transport. *Applied Physics Express*, **2012**, 5, 125501	2.4	33
113	Self-Separation of a Thick AlN Layer from a Sapphire Substrate via Interfacial Voids Formed by the Decomposition of Sapphire. *Applied Physics Express*, **2008**, 1, 045003	2.4	29
112	Theoretical Analysis for Surface Reconstruction of AlN and InN in the Presence of Hydrogen. *Japanese Journal of Applied Physics*, **2007**, 46, 5112-5115	1.4	27
111	High-temperature growth of thick AlN layers on sapphire (0001) substrates by solid source halide vapor-phase epitaxy. *Journal of Crystal Growth*, **2008**, 310, 4016-4019	1.6	26
110	Thermal stability of Ga2O3in mixed flows of H2and N2. *Japanese Journal of Applied Physics*, **2015**, 54, 041102	1.4	24
109	Growth of thick InGaN layers by tri-halide vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 05FL02	1.4	23
108	Thick and high-quality GaN growth on GaAs (1 1 1) substrates for preparation of freestanding GaN. *Journal of Crystal Growth*, **2002**, 246, 215-222	1.6	22
107	Growth of Thick Hexagonal GaN Layer on GaAs (111)A Surfaces for Freestanding GaN by Metalorganic Hydrogen Chloride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2000**, 39, L703-L706	1.4	22
106	Hydride vapor phase epitaxy of InN by the formation of InCl3 using In metal and Cl2. *Journal of Crystal Growth*, **2007**, 300, 57-61	1.6	21
105	In situ gravimetric monitoring of decomposition rate on the surface of (0001) c-plane sapphire for the high temperature growth of AlN. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2297-2300		21
104	Polarities of AlN films and underlying 3C-SiC intermediate layers grown on (111) Si substrates. *Journal of Crystal Growth*, **2008**, 310, 96-100	1.6	21
103	Growth of GaN Directly on Si(111) Substrate by Controlling Atomic Configuration of Si Surface by Metalorganic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2006**, 45, L478-L481	1.4	20
102	Crystal growth of HVPE-GaN doped with germanium. *Journal of Crystal Growth*, **2017**, 480, 102-107	1.6	19
101	Ga2O3 Schottky barrier diodes with nGa2O3 drift layers grown by HVPE **2015**,		17
100	Thermodynamics on hydride vapor phase epitaxy of AlN using AlCl3 and NH3. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1431-1435	1.3	17

99	In situGravimetric Monitoring of Decomposition Rate on Surface of (10bar12)R-Plane Sapphire for High-Temperature Growth of Nonpolar AlN. *Japanese Journal of Applied Physics*, **2008**, 47, 3434-3437	1.4	16
98	Growth of thin protective AlN layers on sapphire substrates at 1065 °C for hydride vapor phase epitaxy of AlN above 1300 °C. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1515-1517		16
97	Control of in-plane epitaxial relationship of c -plane AlN layers grown on a -plane sapphire substrates by hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2028-2030		15
96	Investigation of polarity dependent InN{0001} decomposition in N2 and H2 ambient. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S372-S375		15
95	Preparation of a crack-free AlN template layer on sapphire substrate by hydride vapor-phase epitaxy at 1450 °C. *Journal of Crystal Growth*, **2009**, 311, 2837-2839	1.6	15
94	HVPE growth of $Al_xGa_{1-x}N$ ternary alloy using AlCl3 and GaCl. *Journal of Crystal Growth*, **2007**, 305, 335-339	1.6	15
93	Fe-doped semi-insulating GaN substrates prepared by hydride vapor-phase epitaxy using GaAs starting substrates. *Journal of Crystal Growth*, **2006**, 296, 11-14	1.6	15
92	Preparation of 2-in.-diameter (001) β-Ga2O3homoepitaxial wafers by halide vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2017**, 56, 110310	1.4	14
91	Comparison of O2 and H2O as oxygen source for homoepitaxial growth of β-Ga2O3 layers by halide vapor phase epitaxy. *Journal of Crystal Growth*, **2018**, 492, 39-44	1.6	14
90	Tri-halide vapor phase epitaxy of thick GaN using gaseous GaCl3 precursor. *Journal of Crystal Growth*, **2016**, 456, 140-144	1.6	12
89	Growth of thick and high crystalline quality InGaN layers on GaN (000$\bar{1}$) substrate using tri-halide vapor phase epitaxy. *Journal of Crystal Growth*, **2016**, 456, 145-150	1.6	12
88	First demonstration of vertical Ga2O3 MOSFET: Planar structure with a current aperture **2017**,		12
87	Thermodynamic analysis on HVPE growth of InGaN ternary alloy. *Journal of Crystal Growth*, **2011**, 318, 441-445	1.6	12
86	Formation of AlN on sapphire surfaces by high-temperature heating in a mixed flow of H2 and N2. *Journal of Crystal Growth*, **2012**, 350, 60-65	1.6	11
85	MOVPE-like HVPE of AlN using solid aluminum trichloride source. *Journal of Crystal Growth*, **2007**, 298, 332-335	1.6	11
84	Ab initio calculation for the decomposition process of GaN (0001) and (000$\bar{1}$) surfaces. *Journal of Crystal Growth*, **2008**, 310, 1632-1636	1.6	11
83	Growth of thick AlN layer on sapphire (0001) substrate using hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2062-2065		11
82	Crystallization of semi-insulating HVPE-GaN with solid iron as a source of dopants. *Journal of Crystal Growth*, **2017**, 475, 121-126	1.6	10

81	Tri-halide vapor-phase epitaxy of GaN using GaCl3on polar, semipolar, and nonpolar substrates. *Applied Physics Express*, **2016**, 9, 105501	2.4	10
80	Tri-halide vapor phase epitaxy of GaN using GaCl3 gas as a group III precursor. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1471-1474		10
79	Experimental and ab-initio studies of temperature dependent InN decomposition in various ambient. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1518-1521		10
78	Influence of substrate polarity on the low-temperature GaN buffer layer growth on GaAs (1 1 1)A and (1 1 1)B surfaces. *Journal of Crystal Growth*, **2003**, 247, 245-250	1.6	10
77	Carrier Gas Dependence at Initial Processes fora-Plane AlN Growth onr-Plane Sapphire Substrates by Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 055501	1.4	10
76	Influence of high-temperature processing on the surface properties of bulk AlN substrates. *Journal of Crystal Growth*, **2016**, 446, 33-38	1.6	10
75	Growth of Fe-Doped Thick GaN Layers for Preparation of Semi-Insulating GaN Substrates. *Japanese Journal of Applied Physics*, **2005**, 44, L1072-L1075	1.4	9
74	Growth of thick AlxGa1□N ternary alloy by hydride vapor-phase epitaxy. *Journal of Crystal Growth*, **2007**, 300, 164-167	1.6	8
73	Characterization of a freestanding AlN substrate prepared by hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1512-1514		8
72	Aperture-limited conduction and its possible mechanism in ion-implanted current aperture vertical □Ga2O3 MOSFETs. *Applied Physics Letters*, **2021**, 118, 012102	3.4	8
71	Influence of source gas supply sequence on hydride vapor phase epitaxy of AlN on (0001) sapphire substrates. *Journal of Crystal Growth*, **2012**, 360, 197-200	1.6	7
70	In situ gravimetric monitoring of surface reactions between sapphire and NH3. *Journal of Crystal Growth*, **2009**, 311, 3110-3113	1.6	7
69	Anisotropic complex refractive index of □Ga2O3 bulk and epilayer evaluated by terahertz time-domain spectroscopy. *Applied Physics Letters*, **2021**, 118, 042101	3.4	7
68	Thermodynamic analysis of InGaN-HVPE growth using group-III chlorides, bromides, and iodides. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 413-416		6
67	Ab initio calculation for an initial growth process of GaN on (0001) and (000$ bar 1 $) surfaces by vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S301-S304		6
66	Theoretical investigation on the decomposition process of GaN(0001) surface under a hydrogen atmosphere. *Journal of Crystal Growth*, **2009**, 311, 3103-3105	1.6	6
65	Temperature dependence of InN growth on (0001) sapphire substrates by atmospheric pressure hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2022-2024		6
64	Study of the Decomposition Processes of (0001)AlN in a Hydrogen Atmosphere. *Japanese Journal of Applied Physics*, **2007**, 46, L1114-L1116	1.4	6

63	Temperature dependence of Ga2O3 growth by halide vapor phase epitaxy on sapphire and □Ga2O3 substrates. *Applied Physics Letters*, **2020**, 117, 222101	3.4	6
62	Growth temperatures and the excess chlorine effect of N-Polar GaN growth via tri-halide vapor phase epitaxy. *Journal of Crystal Growth*, **2018**, 502, 7-13	1.6	6
61	Thick nonpolar m-plane and semipolar (101 1) GaN on an ammonothermal seed by tri-halide vapor-phase epitaxy using GaCl3. *Journal of Crystal Growth*, **2017**, 461, 25-29	1.6	5
60	Quasiequilibrium crystal shape and kinetic Wulff plot for GaN grown by trihalide vapor phase epitaxy using GaCl3. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600679	1.3	5
59	High rate InN growth by two-step precursor generation hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2015**, 422, 15-19	1.6	5
58	In situGravimetric Monitoring of Thermal Decomposition and Hydrogen Etching Rates of 6H-SiC(0001) Si Face. *Japanese Journal of Applied Physics*, **2009**, 48, 095505	1.4	5
57	Influence of surface atom arrangement on the growth of InN layers on GaAs (111)A and (111)B surfaces by metalorganic vapor-phase epitaxy. *Journal of Crystal Growth*, **2007**, 298, 387-389	1.6	5
56	A new system for growing thick InN layers by hydride vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 2419-2422		5
55	Influence of hydrogen input partial pressure on the polarity of InN on GaAs (1 1 1)A grown by metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **2008**, 310, 1602-1606	1.6	5
54	Improvements in the crystalline quality of MOVPE-InN layers by facet controlling with hydrogen partial pressure. *Journal of Crystal Growth*, **2008**, 310, 4954-4958	1.6	5
53	Characterization of trap states in buried nitrogen-implanted □Ga2O3. *Applied Physics Letters*, **2020**, 117, 243505	3.4	5
52	Investigation of NH3input partial pressure for N-polarity InGaN growth on GaN substrates by tri-halide vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2016**, 55, 05FA01	1.4	5
51	Stability and degradation of isolation and surface in Ga2O3 devices. *Microelectronics Reliability*, **2019**, 100-101, 113453	1.2	4
50	High-Temperature Heat-Treatment ofc-,a-,r-, andm-Plane Sapphire Substrates in Mixed Gases of H2and N2. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB10	1.4	4
49	Growth of semi-polar InN layer on GaAs (110) surface by MOVPE. *Journal of Crystal Growth*, **2011**, 318, 479-482	1.6	4
48	Selective growth of InN on patterned GaAs(111)B substrate □influence of InN decomposition at the interface. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2019-2021		4
47	Thermodynamic study on the role of hydrogen during hydride vapor phase epitaxy of Alx Ga1□ N. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1457-1460		4
46	Vinyltitanium as an initiator for the polymerization of acetylene. *Journal of Polymer Science Part A*, **2002**, 40, 2663-2669	2.5	4

45	Impact of crystallization manner of the buffer layer on the crystalline quality of GaN epitaxial layers on GaAs (111)A substrate. *Journal of Crystal Growth*, **2005**, 275, e1149-e1154	1.6	4
44	Growth and characterization of thick GaN layers with high Fe doping. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2058-2061		4
43	Thermal and chemical stabilities of group-III sesquioxides in a flow of either N2or H2. *Japanese Journal of Applied Physics*, **2016**, 55, 1202BE	1.4	3
42	First-principles study on the effect of surface hydrogen coverage on the adsorption process of ammonia on InN(0001) surfaces. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2267-2269		3
41	Controlled formation of voids at the AlN/sapphire interface by sapphire decomposition for self-separation of the AlN layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S447-S450		3
40	Influence of substrate polarity of (0 0 0 1) and (0 0 0 $\bar{1}$)GaN surfaces on hydride vapor-phase epitaxy of InN. *Journal of Crystal Growth*, **2010**, 312, 651-655	1.6	3
39	Theoretical investigation of the decomposition mechanism of AlN(0001) surface under a hydrogen atmosphere. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 2265-2267		3
38	High Temperature Ramping Rate for GaAs (111)A Substrate Covered with a Thin GaN Buffer Layer for Thick GaN Growth at 1000℃. *Japanese Journal of Applied Physics*, **2003**, 42, L526-L528	1.4	3
37	Trade-off between thickness and temperature ramping rate of GaN buffer layer studied for high quality GaN growth on GaAs (111)A substrate. *Journal of Crystal Growth*, **2004**, 268, 1-7	1.6	3
36	Fabrication of Semi-Insulating GaN Wafers by Hydride Vapor Phase Epitaxy of Fe-Doped Thick GaN Layers Using GaAs Starting Substrates. *Japanese Journal of Applied Physics*, **2005**, 44, L1519-L1521	1.4	3
35	Thermodynamic analysis of vapor-phase epitaxy of CdTe using a metallic Cd source. *Journal of Crystal Growth*, **2017**, 470, 122-127	1.6	2
34	Hydride vapor phase epitaxy of Si-doped AlN layers using SiCl4 as a doping gas. *Journal of Crystal Growth*, **2020**, 545, 125730	1.6	2
33	Ga2O3 field-plated schottky barrier diodes with a breakdown voltage of over 1 kV **2016**,		2
32	Influence of intermediate layers on thick InGaN growth using tri-halide vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2019**, 58, SC1027	1.4	2
31	Direct Growth of CdTe on a (211) Si Substrate with Vapor Phase Epitaxy Using a Metallic Cd Source. *Journal of Electronic Materials*, **2017**, 46, 5884-5888	1.9	2
30	Current Status of Gallium Oxide-Based Power Device Technology **2015**,		2
29	Effects of substrate nitridation and buffer layer on the crystalline improvements of semi-polar InN(10$\bar{1}$3) crystal on GaAs(110) by MOVPE. *Journal of Crystal Growth*, **2013**, 367, 122-125	1.6	2
28	Carrier Gas Dependence at Initial Processes fora-Plane AlN Growth onr-Plane Sapphire Substrates by Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 055501	1.4	2

27	Theoretical study on the influence of surface hydrogen coverage on the initial growth process of AlN(0001) surfaces. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1577-1580		2
26	Semi-polar InN(10$ bar 1 $3) dominant growth on GaAs(110) substrate by mixing hydrogen in carrier gas. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2025-2027		2
25	Two-Step Growth of (0001) ZnO Single-Crystal Layers on (0001) Sapphire Substrates by Halide Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 125503	1.4	2
24	First principles study of the decomposition processes of AlN in a hydrogen atmosphere. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3042-3044		2
23	Thermodynamic Analysis of Various Types of Hydride Vapor Phase Epitaxy System for High-Speed Growth of InN. *Japanese Journal of Applied Physics*, **2006**, 45, L1203-L1205	1.4	2
22	Vertical Ga_2O_3 Schottky Barrier Diodes with Guard Ring Formed by Nitrogen-Ion Implantation **2019** ,		2
21	Enhancement-Mode Current Aperture Vertical Ga_2O_3 MOSFETs **2019**,		2
20	Effect of substrate orientation on homoepitaxial growth of Ga_2O_3 by halide vapor phase epitaxy. *Applied Physics Letters*, **2022**, 120, 102102	3.4	2
19	**2020**,		1
18	Formation mechanism of AlN whiskers on sapphire surfaces heat-treated in a mixed flow of $H_2$and N_2. *Japanese Journal of Applied Physics*, **2016**, 55, 05FF01	1.4	1
17	GaN growth via tri-halide vapor phase epitaxy using solid source of $GaCl_3$: investigation of the growth dependence on NH_3 and additional Cl_2. *Japanese Journal of Applied Physics*, **2019**, 58, SC1022	1.4	1
16	Suppression of twin formation for the growth of InN(10-1-3) on GaAs(110) by metalorganic vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 472-475		1
15	Effect of High NH_3Input Partial Pressure on Hydride Vapor Phase Epitaxy of InN Using Nitrided (0001) Sapphire Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JD05	1.4	1
14	First-principles calculation and X-ray absorption fine structure analysis of Fe doping mechanism for semi-insulating GaN growth on GaAs substrates. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 1862-1866	1.3	1
13	Halide Vapor Phase Epitaxy 1. *Springer Series in Materials Science*, **2020**, 185-202	0.9	1
12	Recent Advances in Ga_2O_3 MOSFET Technologies **2018**,		1
11	Growth of GaN on a three-dimensional SCAATTM bulk seed by tri-halide vapor phase epitaxy using $GaCl_3$. *Japanese Journal of Applied Physics*, **2019**, 58, SC1024	1.4	0
10	Growth of Highly Crystalline GaN at High Growth Rate by Trihalide Vapor-Phase Epitaxy. *Physica Status Solidi (B): Basic Research*, **2020**, 257, 1900564	1.3	0

9	Vapor Phase Epitaxy of (133) and (211) CdTe on (211) Si Substrates Using Metallic Cd Source. *Journal of Electronic Materials*, **2019**, 48, 454-459	1.9	0
8	Growth of lattice-relaxed InGaN thick films on patterned sapphire substrates by tri-halide vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2021**, 60, 105501	1.4	0
7	Influence of growth temperature on the twin formation of InN{10$ bar 1 $3} on GaAs(110) by metalorganic vapor phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 677-680		
6	Improvements in crystalline quality of thick GaN layers on GaAs (111)A by periodic insertion of low-temperature GaN buffer layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2141-2144		
5	Influence of Temperature Ramping Rate on Thick GaN Growth on GaAs (111)A Surfaces. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 166-169		
4	Gallium Oxide Schottky Barrier Diodes. *IEEJ Transactions on Electronics, Information and Systems*, **2016**, 136, 479-483	0.1	
3	Two-Step Growth of (0001) ZnO Single-Crystal Layers on (0001) Sapphire Substrates by Halide Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 125503	1.4	
2	Dependence of surface morphology at initial growth of CdTe on the II/VI on (2 1 1) Si substrates by vapor phase epitaxy using metallic Cd source. *Journal of Crystal Growth*, **2019**, 506, 185-189	1.6	
1	Facet stability of GaN during tri-halide vapor phase epitaxy: an ab initio-based approach. *CrystEngComm*, **2021**, 23, 1423-1428	3.3	